

IN THE CLAIMS:

Please **amend** claims 1 and 9 to read as follows:

1. (Thrice Amended) A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate, a channel region,
a source region, a drain region, a first insulating layer and a second insulating
layer, wherein:

said channel region, said source region and said drain region comprise
polycrystalline silicon,

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said glass substrate is defined as having a physical property such that its
compaction is 30 ppm or higher, when said glass substrate is heated at 600° C
for 1 hour and thereafter cooled at a rate of 1° C/minute,

said first insulating layer covers said channel region and has a layer
thickness whose lower limit is 4nm, and

said second insulating layer is formed on a surface of said first insulating
layer.

9. (Thrice Amended) A thin-film transistor comprising:

a glass substrate; and

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formed at an upper part of said glass substrate, a channel region, a
source region, a drain region and an insulating layer, wherein:

said channel region, said source region and said drain region comprise
polycrystalline silicon,

said glass substrate is defined as having a physical property such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute, and

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said insulating layer covers said channel region and has a layer thickness defined by the range 4nm to 20nm.
